

Features

- Advanced Trench MOS Technology
- Low Gate Charge
- 100% EAS Tested
- Green Device Available

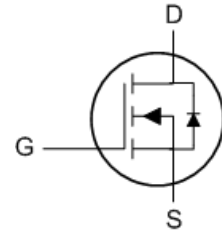
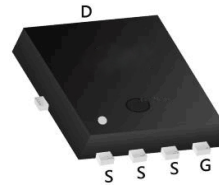
Applications

- Power Management in Desktop Computer
- DC/DC Converters

Product Summary

| BVDSS | RDSON | ID |
|-------|-------|------|
| 30V | 2.0mΩ | 120A |

DFN5X6 Pin Configuration



Absolute Maximum Ratings

| Symbol | Parameter | Rating | Units |
|-----------------------------|--|------------|------------------|
| V_{DS} | Drain-Source Voltage | 30 | V |
| V_{GS} | Gate-Source Voltage | ± 20 | V |
| $I_D@T_C=25^\circ\text{C}$ | Continuous Drain Current, $V_{GS} @ 10V^{1,6}$ | 120 | A |
| $I_D@T_C=100^\circ\text{C}$ | Continuous Drain Current, $V_{GS} @ 10V^{1,6}$ | 76 | A |
| I_{DM} | Pulsed Drain Current ² | 240 | A |
| EAS | Single Pulse Avalanche Energy ³ | 80 | mJ |
| I_{AS} | Avalanche Current | 40 | A |
| $P_D@T_C=25^\circ\text{C}$ | Total Power Dissipation ⁴ | 50 | W |
| T_{STG} | Storage Temperature Range | -55 to 150 | $^\circ\text{C}$ |
| T_J | Operating Junction Temperature Range | -55 to 150 | $^\circ\text{C}$ |

Thermal Data

| Symbol | Parameter | Typ. | Max. | Unit |
|-----------------|--|------|------|--------------------|
| $R_{\theta JA}$ | Thermal Resistance Junction-Ambient ¹ | --- | 60 | $^\circ\text{C/W}$ |
| $R_{\theta JC}$ | Thermal Resistance Junction-Case ¹ | --- | 2.5 | $^\circ\text{C/W}$ |

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

| Symbol | Parameter | Conditions | Min. | Typ. | Max. | Unit |
|---------------------|--|--|------|------|------|------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V, I _D =250uA | 30 | --- | --- | V |
| R _{DS(ON)} | Static Drain-Source On-Resistance ² | V _{GS} =10V, I _D =20A | --- | 1.65 | 2.0 | mΩ |
| | | V _{GS} =4.5V, I _D =20A | --- | 2.45 | 3.3 | |
| V _{GS(th)} | Gate Threshold Voltage | V _{GS} =V _{DS} , I _D =250uA | 1.2 | 1.6 | 2.3 | V |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} =24V, V _{GS} =0V, T _J =25°C | --- | --- | 1 | uA |
| | | V _{DS} =24V, V _{GS} =0V, T _J =55°C | --- | --- | 5 | |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} =±20V, V _{DS} =0V | --- | --- | ±100 | nA |
| g _{fs} | Forward Transconductance | V _{DS} =5V, I _D =20A | --- | 40 | --- | S |
| R _g | Gate Resistance | V _{DS} =0V, V _{GS} =0V, f=1MHz | --- | 2.0 | --- | Ω |
| Q _g | Total Gate Charge (10V) | V _{DS} =15V, V _{GS} =4.5V, I _D =20A | --- | 51.5 | --- | nC |
| Q _g | Total Gate Charge (4.5V) | | --- | 26.1 | --- | |
| Q _{gs} | Gate-Source Charge | | --- | 8 | --- | |
| Q _{gd} | Gate-Drain Charge | | --- | 10.6 | --- | |
| T _{d(on)} | Turn-On Delay Time | V _{DD} =15V, V _{GS} =10V, R _G =3.3Ω, I _D =20A | --- | 11.5 | --- | ns |
| T _r | Rise Time | | --- | 45.5 | --- | |
| T _{d(off)} | Turn-Off Delay Time | | --- | 28.5 | --- | |
| T _f | Fall Time | | --- | 7.1 | --- | |
| C _{iss} | Input Capacitance | V _{DS} =15V, V _{GS} =0V, f=1MHz | --- | 2859 | --- | pF |
| C _{oss} | Output Capacitance | | --- | 1259 | --- | |
| C _{rss} | Reverse Transfer Capacitance | | --- | 229 | --- | |

Diode Characteristics

| | | | | | | |
|-----------------|--|---|-----|-----|-----|----|
| I _S | Continuous Source Current ^{1,6} | V _G =V _D =0V, Force Current | --- | --- | 85 | A |
| V _{SD} | Diode Forward Voltage ² | V _{GS} =0V, I _S =1A, T _J =25°C | --- | --- | 1.2 | V |
| T _{rr} | Reverse Recovery Time | I _F =15A, di/dt=100A/μs, | --- | 35 | --- | nS |
| Q _{rr} | Reverse Recovery Charge | T _J =25°C | --- | 19 | --- | nC |

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=40A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_S , in real applications , should be limited by total power dissipation.
- 6.Package limitation current is 85A.

Typical Characteristics

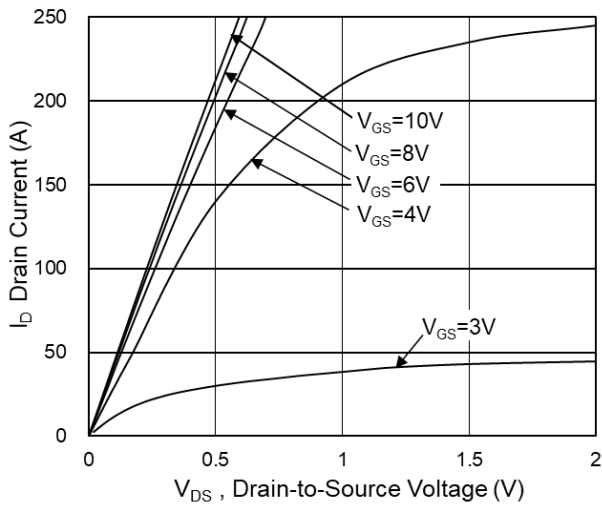


Fig.1 Typical Output Characteristics

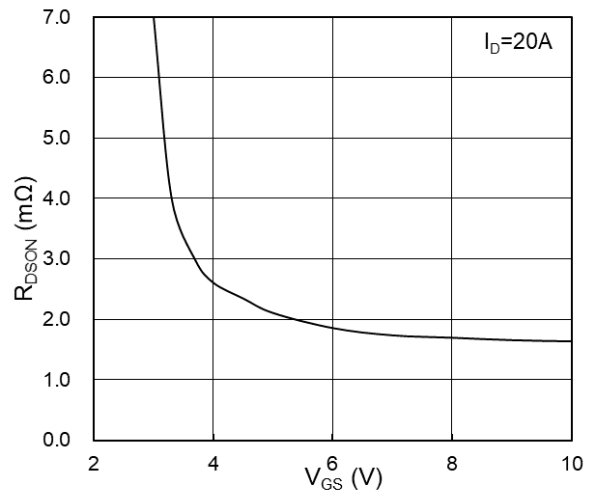


Fig.2 On-Resistance vs G-S Voltage

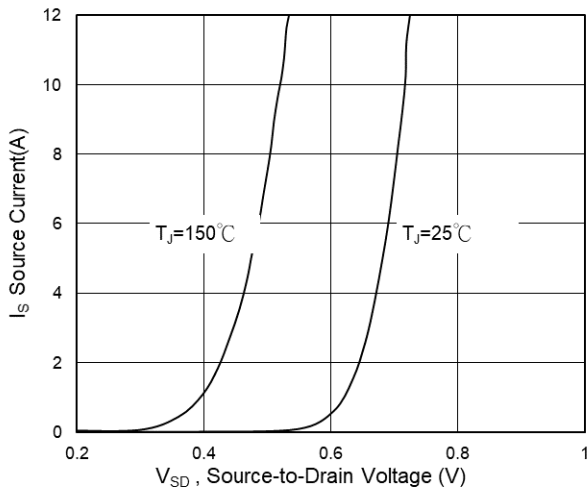


Fig.3 Source Drain Forward Characteristics

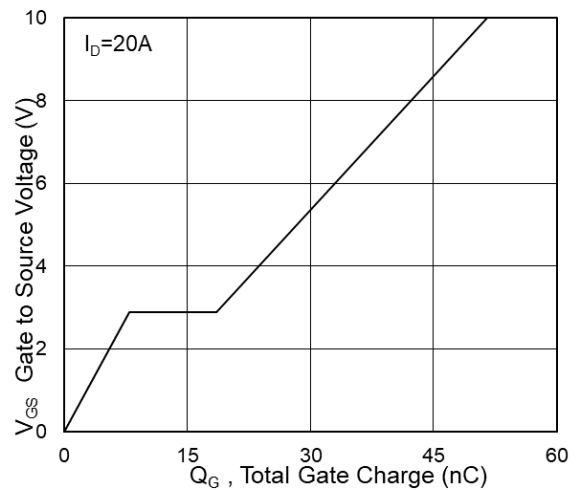


Fig.4 Gate-Charge Characteristics

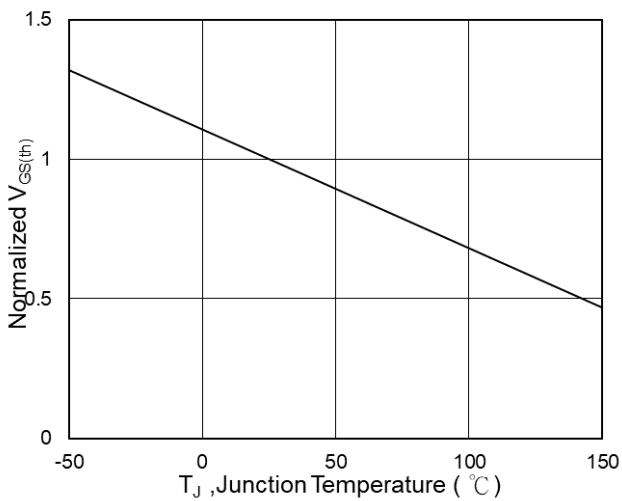


Fig.5 Normalized $V_{GS(th)}$ vs T_J

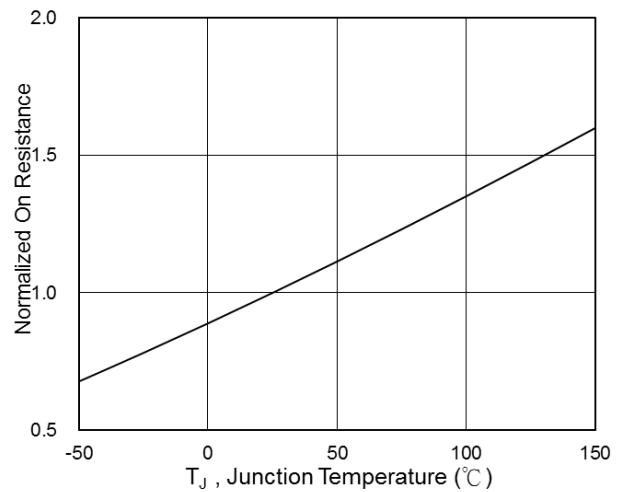


Fig.6 Normalized $R_{DS(on)}$ vs T_J

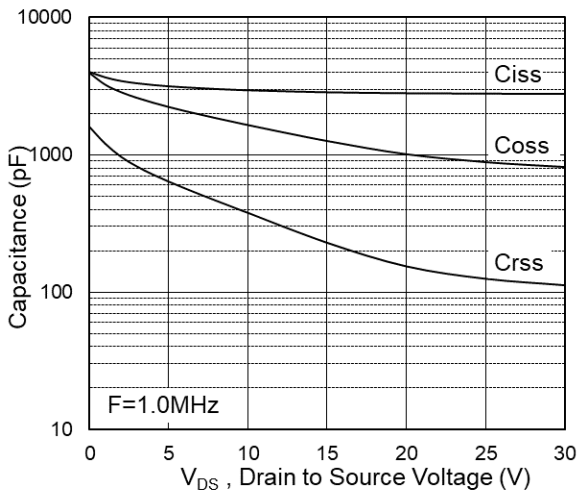


Fig.7 Capacitance

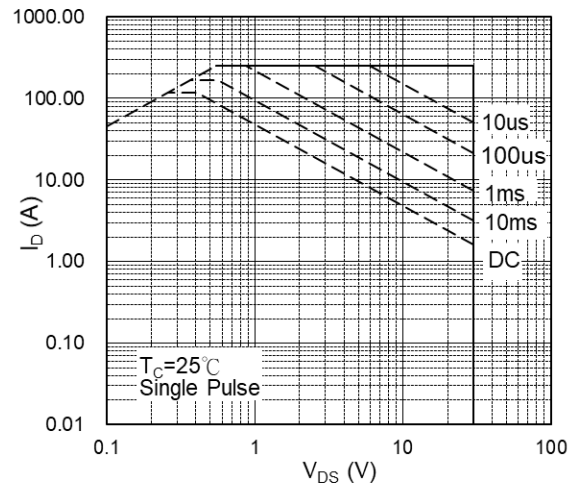


Fig.8 Safe Operating Area

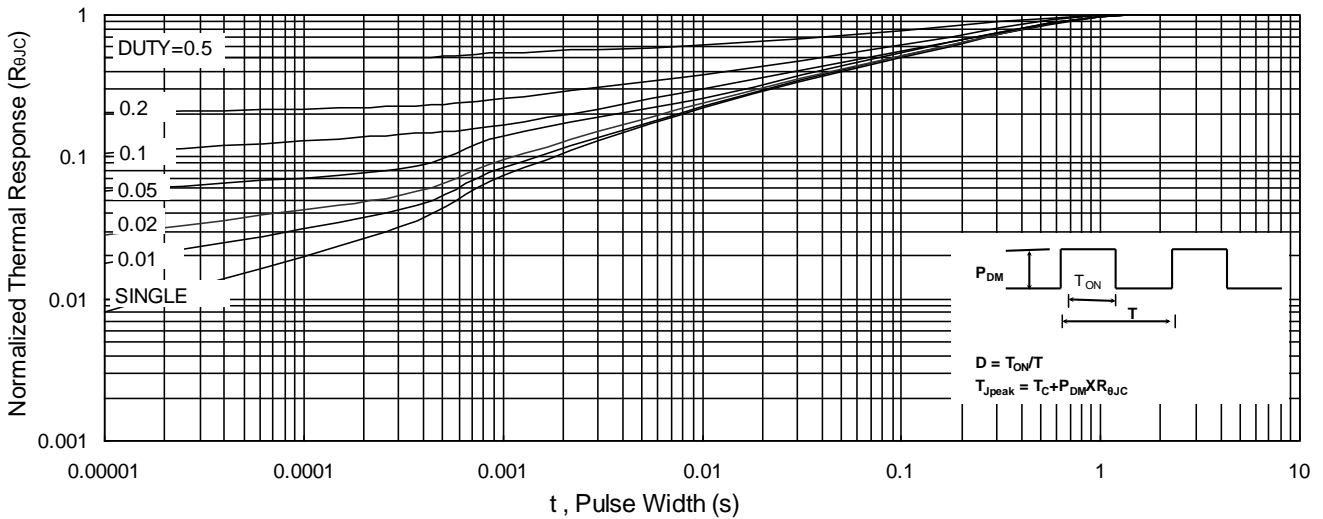


Fig.9 Normalized Maximum Transient Thermal Impedance

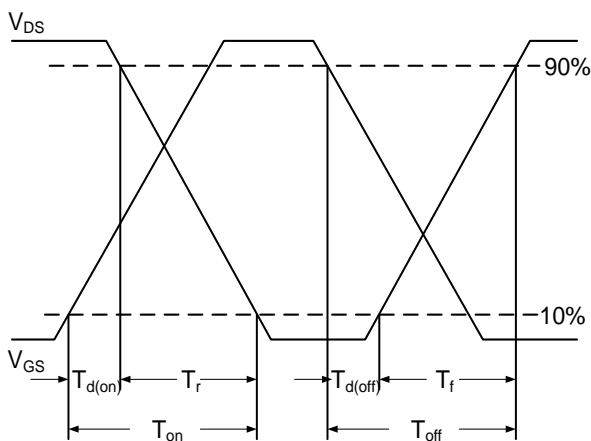


Fig.10 Switching Time Waveform

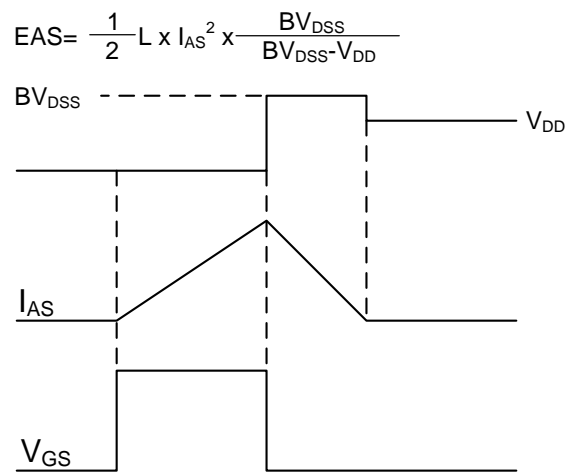
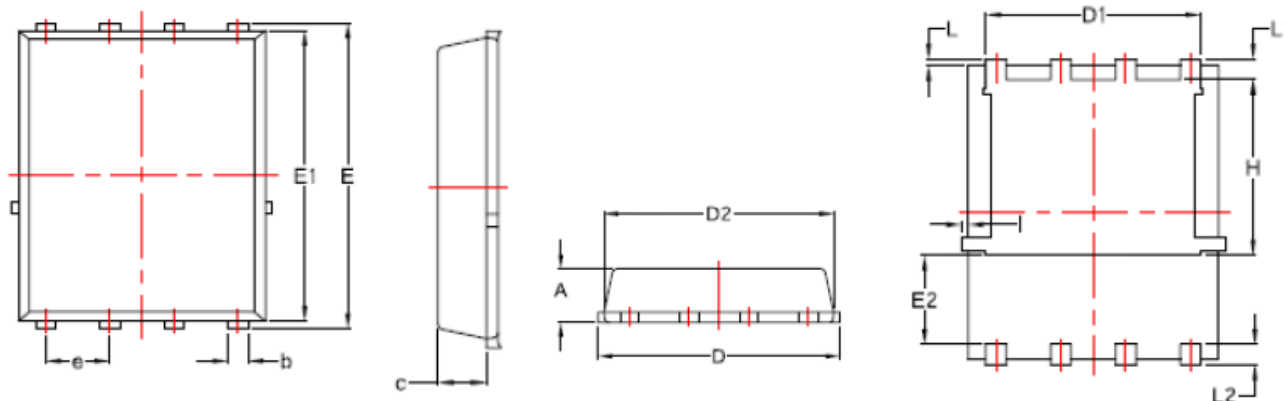


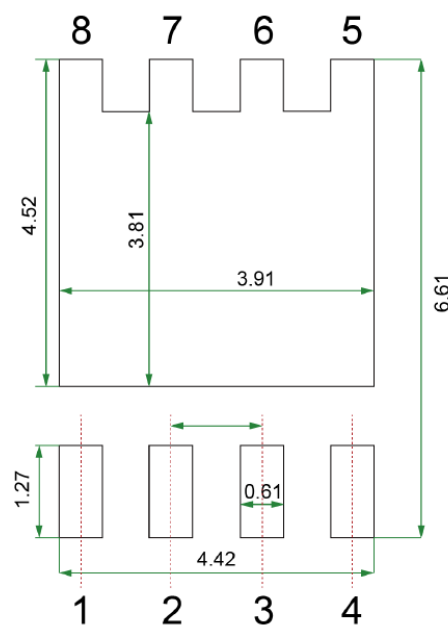
Fig.11 Unclamped Inductive Switching Waveform

DFN5×6 Outline



Land Pattern (Only for Reference)
Unit : mm

| SYMBOLS | MILLIMETERS | | INCHES | |
|---------|-------------|-------|----------|--------|
| | MIN | MAX | MIN | MAX |
| A | 0.90 | 1.20 | 0.0354 | 0.0474 |
| b | 0.30 | 0.51 | 0.0118 | 0.0200 |
| c | 0.60 | 1.046 | 0.0236 | 0.0412 |
| D | 4.80 | 5.45 | 0.1890 | 0.2146 |
| D1 | 4.11 | 4.31 | 0.1618 | 0.1697 |
| D2 | 4.80 | 5.20 | 0.1890 | 0.2047 |
| E | 5.90 | 6.35 | 0.2323 | 0.2500 |
| E1 | 5.65 | 6.06 | 0.2224 | 0.2386 |
| E2 | 1.10 | - | 0.0433 | - |
| e | 1.27 BSC | | 0.05 BSC | |
| L | 0.05 | 0.25 | 0.0020 | 0.0098 |
| L1 | 0.38 | 0.61 | 0.0150 | 0.0240 |
| L2 | 0.30 | 0.71 | 0.0118 | 0.0280 |
| H | 3.30 | 3.92 | 0.1300 | 0.1543 |
| I | - | 0.18 | - | 0.0070 |



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